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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	27
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l041k6t7

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Peripheral	STM32 L041F4	STM32 L041G4	STM32 L041K4	STM32 L041C4	STM32 L041F6	STM32 L041E6	STM32 L041G6	STM32 L041K6	STM32 L041C6
Operating temperatures					perature: –4 perature: –4				
Packages	TSSOP 20	UFQFPN 28	LQFP32, UFQFPN 32	LQFP48	TSSOP 20	WLCSP 25	UFQFPN 28	LQFP32, UFQFPN 32	LQFP48

 Table 2. Ultra-low-power STM32L041x4/x6 device features and peripheral counts (continued)

1. 1 SPI interface is a USART operating in SPI master mode.

2. 23 GPIOs are available only on STM32L041GxUxS part number.

3. LQFP32 has two GPIOs, less than UFQFPN32 (27).

4. HSE external quartz connexion available only on LQFP48.

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Operating power supply	Functionalities depending on the operating power supply range						
range	ADC operation	Dynamic voltage scaling range	I/O operation				
V _{DD} = 1.65 to 1.71 V	Conversion time up to 570 ksps	Range 2 or range 3	Degraded speed performance				
V _{DD} = 1.71 to 2.0 V ⁽¹⁾	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Degraded speed performance				
V _{DD} = 2.0 to 2.4 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Full speed operation				
V _{DD} = 2.4 to 3.6 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Full speed operation				

 CPU frequency changes from initial to final must respect the condition: f_{CPU initial} <4f_{CPU initial}. It must also respect 5 µs delay between two changes. For example to switch from 4.2 MHz to 32 MHz, you can switch from 4.2 MHz to 16 MHz, wait 5 µs, then switch from 16 MHz to 32 MHz.

Table 4. CPU frequency range depending on dynamic voltage scaling

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
32 kHz to 4.2 MHz (0ws)	Range 3

Table 5. Functionalities depending on the working mode(from Run/active down to standby) ⁽¹⁾

			Low-	Low-		Stop	S	Standby
IPs	Run/Active	Sleep	power run	power sleep		Wakeup capability		Wakeup capability
CPU	Y		Y					
Flash memory	0	0	0	0				
RAM	Y	Y	Y	Y	Y			
Backup registers	Y	Y	Y	Y	Y		Y	
EEPROM	0	0	0	0				
Brown-out reset (BOR)	0	0	0	0	0	0	0	0
DMA	0	0	0	0				
Programmable Voltage Detector (PVD)	0	0	0	0	0	0	-	



The Cortex-M0+ processor closely integrates a configurable Nested Vectored Interrupt Controller (NVIC), to deliver industry-leading interrupt performance. The NVIC:

- includes a Non-Maskable Interrupt (NMI)
- provides zero jitter interrupt option
- provides four interrupt priority levels

The tight integration of the processor core and NVIC provides fast execution of Interrupt Service Routines (ISRs), dramatically reducing the interrupt latency. This is achieved through the hardware stacking of registers, and the ability to abandon and restart load-multiple and store-multiple operations. Interrupt handlers do not require any assembler wrapper code, removing any code overhead from the ISRs. Tail-chaining optimization also significantly reduces the overhead when switching from one ISR to another.

To optimize low-power designs, the NVIC integrates with the sleep modes, that include a deep sleep function that enables the entire device to enter rapidly stop or standby mode.

This hardware block provides flexible interrupt management features with minimal interrupt latency.

3.4 Reset and supply management

3.4.1 **Power supply schemes**

- V_{DD} = 1.65 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 1.65 to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.

3.4.2 Power supply supervisor

The devices feature an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

Two versions are available:

- The version with BOR activated at power-on operates between 1.8 V and 3.6 V.
- The other version without BOR operates between 1.65 V and 3.6 V.

After the V_{DD} threshold is reached (1.65 V or 1.8 V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the VDD min value becomes 1.65 V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V. When BOR is not active at power-up, the power ramp-up should guarantee that 1.65 V is reached on V_{DD} at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.



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3.5 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

Clock prescaler

To get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler.

• Safe clock switching

Clock sources can be changed safely on the fly in Run mode through a configuration register.

Clock management

To reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.

• System clock source

Three different clock sources can be used to drive the master clock SYSCLK:

- 1-25 MHz high-speed external (HSE), that can supply a PLL
- 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLL
- Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz). When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a ±0.5% accuracy.

Auxiliary clock source

Two ultra-low-power clock sources that can be used to drive the real-time clock:

- 32.768 kHz low-speed external crystal (LSE)
- 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.

RTC clock sources

The LSI, LSE or HSE sources can be chosen to clock the RTC, whatever the system clock.

• Startup clock

After reset, the microcontroller restarts by default with an internal 2 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.

• Clock security system (CSS)

This feature can be enabled by software. If an HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled. Another clock security system can be enabled, in case of failure of the LSE it provides an interrupt or wakeup event which is generated if enabled.

Clock-out capability (MCO: microcontroller clock output)

It outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, each APB (APB1 and APB2) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.



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3.15.2 Low-power Timer (LPTIM)

The low-power timer has an independent clock and is running also in Stop mode if it is clocked by LSE, LSI or an external clock. It is able to wakeup the devices from Stop mode.

This low-power timer supports the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- Continuous / one shot mode
- Selectable software / hardware input trigger
- Selectable clock source
 - Internal clock source: LSE, LSI, HSI or APB clock
 - External clock source over LPTIM input (working even with no internal clock source running, used by the Pulse Counter Application)
- Programmable digital glitch filter
- Encoder mode

3.15.3 SysTick timer

This timer is dedicated to the OS, but could also be used as a standard downcounter. It is based on a 24-bit downcounter with autoreload capability and a programmable clock source. It features a maskable system interrupt generation when the counter reaches '0'.

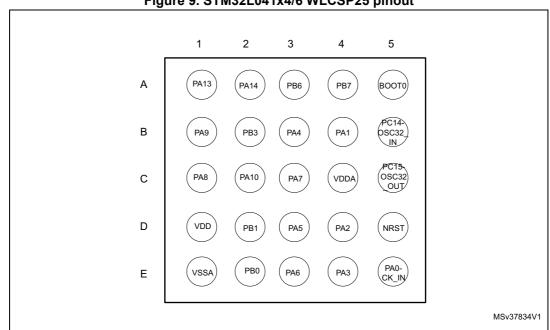
3.15.4 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 37 kHz internal RC and, as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

3.15.5 Window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.





1. The above figure shows the package top view.

		•
ime	Abbreviation	Definition
	Linless otherwise specifie	ed in brackets below the pin name, the pin func

Table 14. Legend/abbreviations used in the pinout table

Nar	ne	Abbreviation Definition					
Pin na	ame		ed in brackets below the pin name, the pin function during ne as the actual pin name				
		S	Supply pin				
Pin t	уре	I	Input only pin				
		I/O	Input / output pin				
		FT	5 V tolerant I/O				
		FTf 5 V tolerant I/O, FM+ capable					
I/O stru	ucture	тс	Standard 3.3V I/O				
		В	Dedicated BOOT0 pin				
		RST	Bidirectional reset pin with embedded weak pull-up resistor				
Not	es	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset.					
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers					
	Additional functions	Functions directly selected	ed/enabled through peripheral registers				

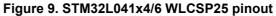




Table 15.	Pin definitions	(continued)

		Pir	n num	ber							,	
TSSOP20	WLCSP25	UFQFPN28	UFQFPN28 (STM32L041GxUxS only)	LQFP32	UFQFPN32 ⁽¹⁾	LQFP48	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	-	-	-	-	-	35	VSS	S	-	-	-	-
-	D1	-	-	-	-	36	VDD	S	-	-	-	-
20	A2	22	22	24	24	37	PA14	I/O	FT	-	SWCLK, LPTIM1_OUT, I2C1_SMBA, USART2_TX, LPUART1_TX	-
-	-	23	23	25	25	38	PA15	I/O	FT	-	SPI1_NSS, TIM2_ETR, EVENTOUT, USART2_RX, TIM2_CH1	
-	B2	24	24	26	26	39	PB3	I/O	FT	-	SPI1_SCK, TIM2_CH2, EVENTOUT	COMP2_INN
-	-	-	25	27	27	40	PB4	I/O	FT	-	SPI1_MISO, EVENTOUT, TIM22_CH1	COMP2_INP
-	-	-	26	28	28	41	PB5	I/O	FT	-	SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM22_CH2	COMP2_INP
-	A3	25	27	29	29	42	PB6	I/O	FTf	-	USART2_TX, I2C1_SCL, LPTIM1_ETR, TIM21_CH1	COMP2_INP
-	A4	26	28	30	30	43	PB7	I/O	FTf	-	USART2_RX, I2C1_SDA, LPTIM1_IN2	COMP2_INP, VREF_PVD_IN



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 17: Voltage characteristics*, *Table 18: Current characteristics*, and *Table 19: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Min	Мах	Unit
V _{DD} -V _{SS}	External main supply voltage (including V _{DDA} , V _{DD}) ⁽¹⁾	-0.3	4.0	
	Input voltage on FT and FTf pins	V _{SS} –0.3	V _{DD} +4.0	
V _{IN} ⁽²⁾	Input voltage on TC pins	V _{SS} –0.3	4.0	V
VIN' /	Input voltage on BOOT0	V _{SS}	V _{DD} +4.0	
	Input voltage on any other pin	V _{SS} –0.3	4.0	
$ \Delta V_{DD} $	Variations between different V_{DDx} power pins	-	50	
V _{DDA} -V _{DDx}	Variations between any V_{DDx} and V_{DDA} power $\mbox{pins}^{(3)}$	-	300	mV
$ \Delta V_{SS} $	Variations between all different ground pins	-	50	
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Sect		

Table 17	Voltage	characteristics
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1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. V_{IN} maximum must always be respected. Refer to *Table 18* for maximum allowed injected current values.

3. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and device operation.



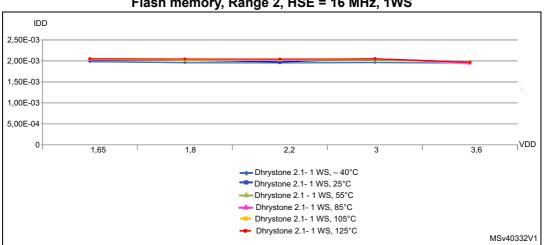
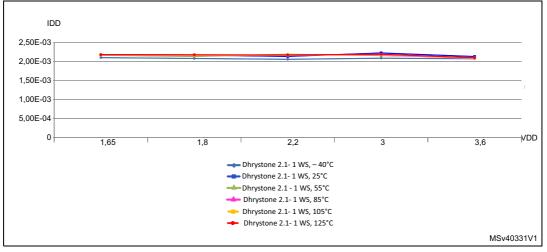


Figure 15. I_{DD} vs V_{DD} , at T_A = 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE = 16 MHz, 1WS

Figure 16. I_{DD} vs V_{DD}, at T_A= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSI16, 1WS





Electrical characteristics

Symbol	Parameter	Conditions	Тур	Мах	Unit
t _{WUSLEEP}	Wakeup from Sleep mode	f _{HCLK} = 32 MHz	7	8	
t _{WUSLEEP}	Wakeup from Low-power sleep mode,	f _{HCLK} = 262 kHz Flash memory enabled	7	8	Number of clock
LP	f _{HCLK} = 262 kHz	f _{HCLK} = 262 kHz Flash memory switched OFF	9	10	cycles
	Wakeup from Stop mode, regulator in Run wode	f _{HCLK} = f _{MSI} = 4.2 MHz	5.0	8	
		f _{HCLK} = f _{HSI} = 16 MHz	4.9	7	
		f _{HCLK} = f _{HSI} /4 = 4 MHz	8.0	11]
		f _{HCLK} = f _{MSI} = 4.2 MHz Voltage range 1	5.0	8	
		f _{HCLK} = f _{MSI} = 4.2 MHz Voltage range 2	5.0	8	
		f _{HCLK} = f _{MSI} = 4.2 MHz Voltage range 3	5.0	8	
		f _{HCLK} = f _{MSI} = 2.1 MHz	7.3	13	
t _{WUSTOP}		f _{HCLK} = f _{MSI} = 1.05 MHz	13	23	
		f _{HCLK} = f _{MSI} = 524 kHz	28	38	μs
		f _{HCLK} = f _{MSI} = 262 kHz	51	65	
		f _{HCLK} = f _{MSI} = 131 kHz	100	120	
		f _{HCLK} = MSI = 65 kHz	200	260	
		f _{HCLK} = f _{HSI} = 16 MHz	4.9	7	
		f _{HCLK} = f _{HSI} /4 = 4 MHz	8.0	11	
		f _{HCLK} = f _{HSI} = 16 MHz	4.9	7	
	Wakeup from Stop mode, regulator in low- power mode, code running from RAM	f _{HCLK} = f _{HSI} /4 = 4 MHz	7.9	10	
		f _{HCLK} = f _{MSI} = 4.2 MHz	4.7	8	
+	Wakeup from Standby mode FWU bit = 1	f _{HCLK} = MSI = 2.1 MHz	65	130	
^t wustdby	Wakeup from Standby mode FWU bit = 0	f _{HCLK} = MSI = 2.1 MHz	2.2	3	ms

Table 36	Low-power	. mode v	wakeun	timinas
	LOW-POWCI	mode	wancup	unnigs



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 25 MHz crystal/ceramic resonator oscillator (LQFP48 package only). All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 39*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit		
f _{OSC_IN}	Oscillator frequency	-	1		25	MHz		
R _F	Feedback resistor	-	-	200	-	kΩ		
G _m	Maximum critical crystal transconductance	Startup	-	-	700	μΑ /V		
t _{SU(HSE)}	Startup time	V_{DD} is stabilized	-	2	-	ms		

Table 39. HSE	oscillator	characteristics ⁽¹⁾
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1. Guaranteed by design.

2. Guaranteed by characterization results. t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 22*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

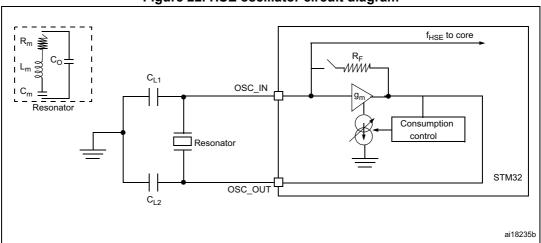


Figure 22. HSE oscillator circuit diagram



Symbol	Parameter	Condition	Тур	Max	Unit
		MSI range 0	30	-	
		MSI range 1	20	-	
		MSI range 2	15	-	
		MSI range 3	10	-	
t	MSI oscillator startup time	MSI range 4	6	-	μs
t _{SU(MSI)}		MSI range 5	5	-	μ5
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	
		MSI range 0	-	40	
		MSI range 1	-	20	
	MSI oscillator stabilization time	MSI range 2	-	10	- µs
		MSI range 3	-	4	
t _{STAB(MSI)} ⁽²⁾		MSI range 4	-	2.5	
'STAB(MSI)		MSI range 5	-	2	μο
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
f	MSL occillator fraguency aversheet	Any range to range 5	-	4	MHz
f _{OVER(MSI)}	MSI oscillator frequency overshoot	Any range to range 6	-	6	

1. This is a deviation for an individual part, once the initial frequency has been measured.

2. Guaranteed by characterization results.

6.3.8 PLL characteristics

The parameters given in *Table 44* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

Symbol	Parameter		Unit		
Symbol	Falanetei	Min	Тур	Max ⁽¹⁾	Unit
f _{PLL_IN}	PLL input clock ⁽²⁾	2	-	24	MHz
	PLL input clock duty cycle	45	-	55	%



	D				
Symbol	Parameter	Min	Тур	Max ⁽¹⁾	Unit
f _{PLL_OUT}	PLL output clock	2	-	32	MHz
t _{LOCK}	PLL input = 16 MHz PLL VCO = 96 MHz	-	115	160	μs
Jitter	Cycle-to-cycle jitter	-		±600	ps
I _{DDA} (PLL)	Current consumption on V _{DDA}	-	220	450	
I _{DD} (PLL)	Current consumption on V _{DD}	-	120	150	- μΑ

Table 44. PLL characteristics (continued)

1. Guaranteed by characterization results.

2. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT} .

6.3.9 Memory characteristics

RAM memory

Table 45. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VRM	Data retention mode ⁽¹⁾	STOP mode (or RESET)	1.65	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Flash memory and data EEPROM

Table 46. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
V _{DD}	Operating voltage Read / Write / Erase	-	1.65	-	3.6	V
+	Programming time for	Erasing	-	3.28	3.94	ms
t _{prog}	word or half-page	Programming	-	3.28	3.94	1115
	Average current during the whole programming / erase operation		-	500	700	μA
I _{DD}	Maximum current (peak) during the whole programming / erase operation	T _A = 25 °C, V _{DD} = 3.6 V	-	1.5	2.5	mA

1. Guaranteed by design.



6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 48*. They are based on the EMS levels and classes defined in application note AN1709.

Syr	mbol	Parameter	Conditions	Level/ Class
V_{FE}	SD	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP48, T _A = +25 °C, f _{HCLK} = 32 MHz conforms to IEC 61000-4-2	3B
V _{EF}	тв	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3$ V, LQFP48, $T_A = +25$ °C, f _{HCLK} = 32 MHz conforms to IEC 61000-4-4	4A

Table 48. EMS characteristics

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.



Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 27* and *Table 55*, respectively.

Unless otherwise specified, the parameters given in *Table 55* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

OSPEEDRx [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions		Max ⁽²⁾	Unit
00	f	Maximum frequency ⁽³⁾	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz
	f _{max(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	100	KI
	t _{f(IO)out}	Output rise and fall time	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns
	t _{r(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	320	115
	f	Maximum frequency ⁽³⁾	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	2 MHz
01	f _{max(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	0.6	
01	t _{f(IO)out}	Output rise and fall time	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	30	ns
	t _{r(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	65	115
	F	Maximum frequency ⁽³⁾	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz
10	F _{max(IO)out}	Maximum requency.	C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2	
10	t _{f(IO)out}	Output rise and fall time	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	V to 3.6 V - 1	13	
	t _{r(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	28	ns
	E	Maximum frequency ⁽³⁾	C_{L} = 30 pF, V_{DD} = 2.7 V to 3.6 V	- 35	35	MHz
11	F _{max(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	10	
	t _{f(IO)out}	Output rise and fall time	C_{L} = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	6	20
	t _{r(IO)out}	Output rise and fall time	C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	17	ns
	f _{max(IO)out}	Maximum frequency ⁽³⁾		-	1	MHz
	t _{f(IO)out}	Output fall time	C _L = 50 pF, V _{DD} = 2.5 V to 3.6 V -		10	ns
Fm+ configuration ⁽⁴⁾	t _{r(IO)out}	Output rise time			30	
	f _{max(IO)out}	Maximum frequency ⁽³⁾		-	350	KHz
	t _{f(IO)out}	Output fall time	C _L = 50 pF, V _{DD} = 1.65 V to 3.6 V -		15	
	t _{r(IO)out}	Output rise time	1	-	60	ns
-	t _{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	ns

 Table 55. I/O AC characteristics⁽¹⁾

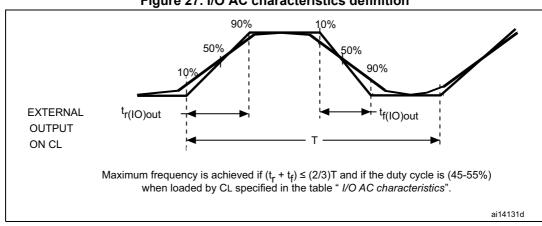
1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.

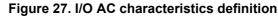
2. Guaranteed by design.

3. The maximum frequency is defined in *Figure* 27.

4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the line reference manual for a detailed description of Fm+ I/O configuration.







6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} , except when it is internally driven low (see *Table 56*).

Unless otherwise specified, the parameters given in *Table 56* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)} ⁽¹⁾	NRST input low level voltage	-	V_{SS}	-	0.8	
V _{IH(NRST)} ⁽¹⁾	NRST input high level voltage	-	1.4	-	V_{DD}	
V _{OL(NRST)} ⁽¹⁾	NRST output low level	I _{OL} = 2 mA 2.7 V < V _{DD} < 3.6 V	-	-	0.4	V
	voltage	I _{OL} = 1.5 mA 1.65 V < V _{DD} < 2.7 V	-	-	0.4	
V _{hys(NRST)} ⁽¹⁾	NRST Schmitt trigger voltage hysteresis	-	-	10%V _{DD} ⁽²⁾	-	mV
R _{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	30	45	60	kΩ
V _{F(NRST)} ⁽¹⁾	NRST input filtered pulse	-	-	-	50	ns
V _{NF(NRST)} ⁽¹⁾	NRST input not filtered pulse	-	350	_	-	ns

Table	56.	NRST	nin	characteristics
Iable	50.		pill	characteristics

1. Guaranteed by design.

2. 200 mV minimum value

3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.



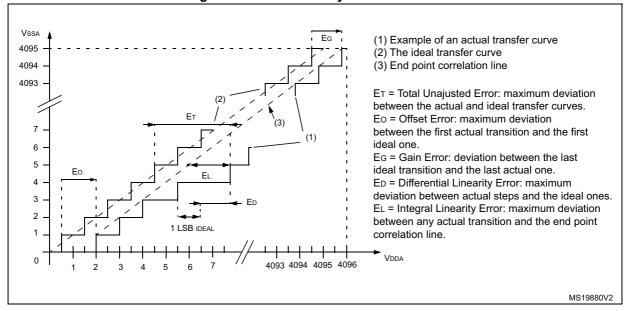
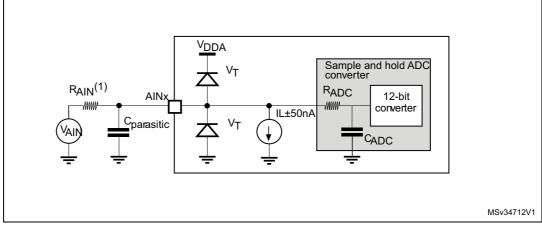


Figure 29. ADC accuracy characteristics





^{1.} Refer to Table 57: ADC characteristics for the values of RAIN, RADC and CADC.

C_{parasitic} represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high C_{parasitic} value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

6.3.16 Temperature sensor characteristics

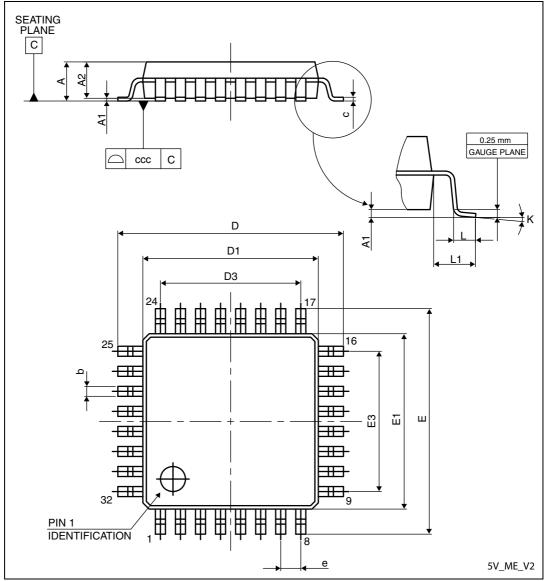
Table 60. Temperature sensor calibration values

Calibration value name	Description	Memory address		
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, V _{DDA} = 3 V	0x1FF8 007A - 0x1FF8 007B		
TS_CAL2	TS ADC raw data acquired at temperature of 130 °C V _{DDA} = 3 V	0x1FF8 007E - 0x1FF8 007F		



7.2 LQFP32 package information

Figure 37. LQFP32, 7 x 7 mm, 32-pin low-profile quad flat package outline



1. Drawing is not to scale.

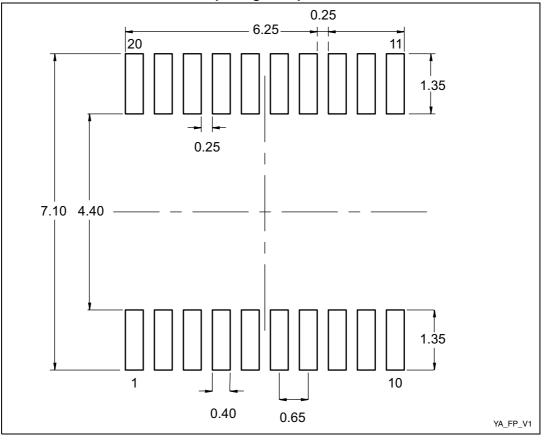


Table 76. TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch,
package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Тур.	Max.	Min.	Тур.	Max.
k	0°	-	8°	0°	-	8°
aaa	-	-	0.100	-	-	0.0039

1. Values in inches are converted from mm and rounded to four decimal digits.

Figure 50. TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch, package footprint



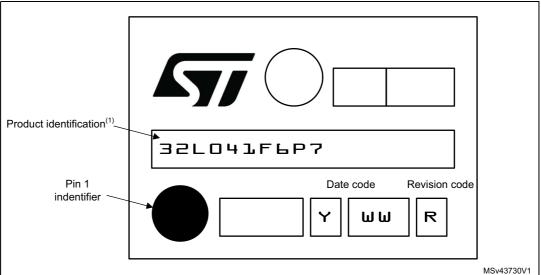
1. Dimensions are expressed in millimeters.



TSSOP20 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depends assembly location, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

